



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-89 Plastic-Encapsulate Transistors

BCX55 TRANSISTOR (NPN)

FEATURES

Power dissipation

P_{CM} : 0.5 W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : 1 A

Collector-base voltage

$V_{(BR)CBO}$: 60 V

Operating and storage junction temperature range

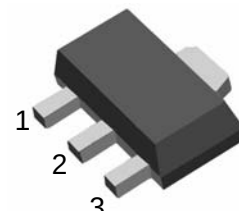
T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

SOT-89

1. BASE

2. COLLECTOR

3. EMITTER



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	60		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10mA, I_B=0$	60		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	5		V
Collector cut-off current	I_{CBO}	$V_{CB}=30V, I_E=0$		0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5V, I_C=0$		0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=2V, I_C=150mA$	63 63 100	250 160 250	
	$h_{FE(2)}$	$V_{CE}=2V, I_C=5mA$	40		
	$h_{FE(3)}$	$V_{CE}=2V, I_C=500mA$	25		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500mA, I_B=50mA$		0.5	V
Base-emitter voltage	$V_{BE(ON)}$	$I_C=500mA, V_{CE}=2V$		1	V
Transition frequency	f_T	$V_{CE}=10V, I_C=50mA$ $f=100MHz$	130		MHz

DEVICE MARKING	BCX55=BE BCX55-10=BG BCX55-16=BM
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